

Abstract of the Disclosure:

5 In a semiconductor memory, a barrier layer formed of a first metal film, a metal nitride film and a second metal film laminated in the named order is formed under a lower electrode of a ferroelectric capacitor in a memory cell, in order to minimize a peeling and lifting of the lower electrode from an underlying plug in the process of forming a ferroelectric material film as a capacitor dielectric film and in its succeeding annealing process. The metal nitride film is formed of a nitride of a metal constituting the first or second metal film.